

23. (New) The method of Claim 21, wherein the metal oxide is RuO₂, IrO₂ or an alloy oxide containing Ru or Ir. B

24. (New) The method of Claim 21, wherein the conductive film is composed of copper or a copper alloy. SUB
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25. (New) The method of Claim 21 further comprising the step of, before forming the barrier metal film, forming an insulating film on the substrate, and thereafter forming a recess in the insulating film, A1

wherein the step of forming the barrier metal film includes a step of forming the barrier metal film on wall surfaces of the recess, and

wherein the step of forming the conductive film includes a step of forming the conductive film on the barrier metal film such that the recess is buried, and thereby forming an embedded wiring composed of the conductive film.

26. (New) The method of Claim 21, wherein the barrier metal film is composed of the metal, and

wherein the step of forming the conductive film includes a step of forming a seed layer on the barrier metal film, and thereafter forming the conductive film on the seed layer by an electroplating process. B

27. (New) The method of Claim 26, wherein the metal composing the barrier metal film is partially oxidized in the step of forming the conductive film.

28. (New) The method of Claim 21, wherein the barrier metal film is composed of the conductive metal oxide, and

wherein the step of forming the conductive film includes a step of forming a seed layer on the barrier metal film, and thereafter forming the conductive film on the seed layer by an electroplating process.

29. (New) The method of Claim 28, wherein the entire barrier metal film is composed of the conductive metal oxide.

30. (New) The method of Claim 21, wherein the barrier metal film is composed of the metal, and

wherein the step of forming the conductive film includes a step of forming the conductive film by an oxidation-reduction reflow process.

31. (New) The method of Claim 30, wherein the conductive metal oxide composing the barrier metal film is oxidized in the step of forming the conductive film.

32. (New) The method of Claim 21 further comprising the step of, after forming the conductive film, forming a wiring of the conductive film by etching the conductive film using a mask pattern covering a wiring forming region.--

REMARKS

The Examiner's Office Action dated April 23, 2002 has been received and its contents carefully noted. Applicant respectfully submits that this response is timely filed and fully response to the Office Action.

Claims 1-20 were pending in the present application prior to the above-noted amendment. By the above amendment, claims 7-20 are canceled without prejudice and new claims 21-32 are added. It is respectfully submitted that no issue of new matter is set forth by this amendment. Accordingly, claims 1-6 and 21-32 are currently pending.